## CS1088

## Vacuum Fluorescent Display Tube Driver

The VFD Driver is a microprocessor interface IC that drives a multiplexed VF (Vacuum Fluorescent) display tube. It consists of a 34-bit shift register, a 34-bit transparent data latch, a metal mask ROM, six 20 mA anode output drivers, twenty-five 2 mA anode output drivers, and three 50 mA grid drivers with output enables.

## Features

- Power On Reset
- Display Dimming Possible
- Three, 50 mA Grid Drivers
- Anodes:
- 6 @ 20 mA
$-25 @ 2 \mathrm{~mA}$




## ON Semiconductor ${ }^{\text {w }}$

## http://onsemi.com



ORDERING INFORMATION*

| Device | Package | Shipping |
| :---: | :---: | :---: |
| CS1088XN40 | DIP-40 | 9 Units/Rail |

*For additional package options, consult your local ON Semiconductor sales office.

DEVICE MARKING INFORMATION
See general marking information in the device marking section on page 7 of this data sheet.

Figure 1. Application Diagram

## MAXIMUM RATINGS*

| Parameter |  | Value | Unit |
| :---: | :---: | :---: | :---: |
| Supply Voltage ( $\mathrm{V}_{\mathrm{BB}}$ ) |  | -0.6 to +18 | V |
| Input Voltages ( $\mathrm{D}_{\mathrm{IN}}, \mathrm{CLK}$, STB, GREN) |  | -0.6 to +6.0 | V |
| Junction Temperature Range |  | -40 to +150 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range |  | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |
| ESD Susceptibility (Human Body Model) |  | 2.0 | kV |
| ESD Susceptibility (Machine Model) |  | 200 | V |
| Package Thermal Resistance, DIP-40 <br> Junction-to-Case, R QJC <br> Junction-to-Ambient, R QJA |  | $\begin{aligned} & 20 \\ & 45 \end{aligned}$ | $\begin{aligned} & { }^{\circ} \mathrm{C} / \mathrm{W} \\ & { }^{\circ} \mathrm{C} / \mathrm{W} \end{aligned}$ |
| Lead Temperature Soldering: | Wave Solder (through hole styles only) Note 1 Reflow (SMD styles only) Note 2 | 260 Peak 230 Peak | ${ }^{\circ} \mathrm{C}$ |

1. 10 second maximum.
2. 60 second maximum above $183^{\circ} \mathrm{C}$.
*The maximum package power dissipation must be observed.

ELECTRICAL CHARACTERISTICS (8.0 V $\leq \mathrm{V}_{\mathrm{BB}} \leq 16.5 \mathrm{~V}$, Gnd $=0 \mathrm{~V},-40^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{J}} \leq 105^{\circ} \mathrm{C}$; unless otherwise stated. Note 3.)

| Parameter | Test Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{BB}}$ Input |  |  |  |  |  |
| $\mathrm{V}_{\mathrm{BB}}$ Input Voltage | - | 8.0 | - | 16.5 | V |
| $\mathrm{I}_{\mathrm{BB} 0}$ Current | No outputs active, $\mathrm{V}_{\mathrm{BB}}=16.5 \mathrm{~V}$ | - | 2.0 | 5.0 | mA |
| Reset Mode | All outputs forced low. | - | 6.5 | 7.5 | V |

$\mathrm{D}_{\text {IN }}, \mathrm{CLK}, \mathrm{STB}$ Inputs

| $\mathrm{V}_{\mathrm{IL} 1}$, Input Low Voltage | - | - | - | 1.6 | V |
| :--- | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{~V}_{\mathrm{IH}}$, Input High Voltage | - | 3.3 | - | - | V |
| $\mathrm{I}_{\mathrm{IL}}$, Input Current | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IH}}$ | - | 7.5 | 20.0 | $\mu \mathrm{~A}$ |

## GREN Input

| $\mathrm{V}_{\mathrm{IL}}$, Input Low Voltage | - | - | - | 1.6 | V |
| :--- | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{~V}_{\mathrm{IH}}$, Input High Voltage | - | 3.3 | - | - | V |
| $\mathrm{I}_{\mathrm{IH}}$, Input Pull-down Current | $\mathrm{V}_{\mathrm{IN}}=3.325 \mathrm{~V}$ | - | 30 | 60 | $\mu \mathrm{~A}$ |

GRID1, GRID2, GRID3 Outputs

| $\mathrm{I}_{\mathrm{OL}}$ | Sink Current | 1.0 | - | - | mA |
| :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{I}_{\mathrm{OH}}$ | Source Current | 50 | - | - | mA |
| $\mathrm{V}_{\mathrm{OL}}$ | $\mathrm{I}_{\text {OUT }}=1.0 \mathrm{~mA}$ | - | - | 0.5 | V |
| $\mathrm{~V}_{\mathrm{OH}}$ | $\mathrm{I}_{\text {OUT }}=-50 \mathrm{~mA}, \mathrm{~V}_{\mathrm{BB}}=12 \mathrm{~V}$ | $\mathrm{~V}_{\mathrm{BB}}-0.75$ | - | $\mathrm{V}_{\mathrm{BB}}$ | V |

AN24 - AN29 Outputs

| $\mathrm{IOL}_{\mathrm{OL}}$ | Sink Current | 400 | - | - |
| :--- | :--- | :--- | :--- | :--- |
| $\mathrm{I}_{\mathrm{OH}}$ | Source Current | 20 | - | - |
| $\mathrm{V}_{\mathrm{OL}}$ | $\mathrm{I}_{\mathrm{OUT}}=400 \mu \mathrm{~A}$ | - | - | mA |
| $\mathrm{V}_{\mathrm{OH}}$ | $\mathrm{I}_{\mathrm{OUT}}=-20 \mathrm{~mA}, \mathrm{~V}_{\mathrm{BB}}=12 \mathrm{~V}$ | $\mathrm{~V}_{\mathrm{BB}}-0.5$ | - | 0.5 |

3. Designed to meet these characteristics over the stated voltage and temperature ranges, though may not be $100 \%$ parametrically tested in production.

ELECTRICAL CHARACTERISTICS (continued) ( $8.0 \mathrm{~V} \leq \mathrm{V}_{\mathrm{BB}} \leq 16.5 \mathrm{~V}$, Gnd $=0 \mathrm{~V},-40^{\circ} \mathrm{C} \leq \mathrm{T}_{\mathrm{J}} \leq 105^{\circ} \mathrm{C}$; unless otherwise stated. Note 4.)

| Parameter | Test Conditions | Min | Typ | Max | Unit |
| :--- | :--- | :---: | :---: | :---: | :---: | :---: |
| AN1 - AN23 Outputs |  |  |  |  |  |
| $\mathrm{I}_{\mathrm{OL}}$ | Sink Current | 100 | - | - | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\mathrm{OH}}$ | Source Current | 2.0 | - | - | mA |
| $\mathrm{V}_{\mathrm{OL}}$ | $\mathrm{I}_{\mathrm{OUT}}=100 \mu \mathrm{~A}$ | - | - | 0.5 | V |
| $\mathrm{~V}_{\mathrm{OH}}$ | $\mathrm{I}_{\mathrm{OUT}}=-2.0 \mathrm{~mA}, \mathrm{~V}_{\mathrm{BB}}=12 \mathrm{~V}$ | $\mathrm{~V}_{\mathrm{BB}}-0.5$ | - | $\mathrm{V}_{\mathrm{BB}}$ | V |

AC Characteristics: Input and Output Timing

| $\mathrm{F}_{\mathrm{C}}$, CLK Frequency | - | 0 | - | 1.0 | MHz |
| :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{T}_{\mathrm{CL}}$, CLK Low Time | - | 200 | - | - | ns |
| $\mathrm{T}_{\mathrm{CH}}$, CLK High Time | - | 200 | - | - | ns |
| $\mathrm{T}_{\mathrm{CR}}$, CLK Rise Time | - | - | - | 100 | ns |
| $\mathrm{~T}_{\mathrm{CF}}$, CLK Fall Time | - | - | - | 100 | ns |
| $\mathrm{~T}_{\mathrm{SC}}$, STB Low to CLK High Time | - | 50 | - | - | ns |
| $\mathrm{T}_{\mathrm{ST}}$, STB High Time | - | 500 | - | - | ns |
| $\mathrm{T}_{\text {AN }}$, STB High to Anode Output <br> Propagation Delay | - | - | - | 5.0 | $\mu \mathrm{~s}$ |
| $\mathrm{~T}_{\mathrm{GL}}$, Grid Turn On Propagation Delay |  |  |  |  |  |
| $\mathrm{T}_{\mathrm{G} 0}$, Grid Turn Off Propagation Delay | $\mathrm{V}_{\mathrm{BB}}=12 \mathrm{~V}$ | $\mathrm{~V}_{\mathrm{BB}}=12 \mathrm{~V}$ | - | - | 2.0 |
| $\mathrm{~T}_{\mathrm{GR}}$, Grid Rise Time | At rated load. Note 5 | - | - | 5.0 | $\mu \mathrm{~s}$ |
| $\mathrm{~T}_{\mathrm{GF}}$, Grid Fall Time | At rated load. Note 5 | 0.50 | - | 2.00 | $\mu \mathrm{~s}$ |
| $\mathrm{~T}_{\mathrm{AR}}$, Anode Rise Time | At rated load. Note 5 | 0.35 | - | 2.00 | $\mu \mathrm{~s}$ |
| $\mathrm{~T}_{\mathrm{AF}}$, Anode Fall Time | At rated load. Note 5 | 0.40 | - | 2.00 | $\mu \mathrm{~s}$ |

4. Designed to meet these characteristics over the stated voltage and temperature ranges, though may not be $100 \%$ parametrically tested in production.
5. Grid and anode rise / fall times are measured from $10 \%$ and $90 \%$ points. Output currents are at the maximum rated currents for the respective stages.

## PACKAGE LEAD DESCRIPTION

| Package Lead Number | Lead Symbol |  |
| :---: | :---: | :---: |
| 40L DIP | (31 Anode Configuration) | Function |
| 1 | GRID1 | 50 mA grid output. |
| 2 | GRID2 | 50 mA grid output. |
| 3 | GRID3 | 50 mA grid output. |
| 4 | AN1 | 2.0 mA anode output. |
| 5 | AN2 | 2.0 mA anode output. |
| 6 | AN3 | 2.0 mA anode output. |
| 7 | AN4 | 2.0 mA anode output. |
| 8 | AN5 | 2.0 mA anode output. |
| 9 | AN6 | 2.0 mA anode output. |
| 10 | AN7 | 2.0 mA anode output. |
| 11 | AN8 | 2.0 mA anode output. |
| 12 | AN9 | 2.0 mA anode output. |
| 13 | AN10 | 2.0 mA anode output. |
| 14 | AN11 | 2.0 mA anode output. |
| 15 | AN12 | 2.0 mA anode output. |
| 16 | AN13 | 2.0 mA anode output. |
| 17 | AN14 | 2.0 mA anode output. |
| 18 | AN15 | 2.0 mA anode output. |
| 19 | AN16 | 2.0 mA anode output. |
| 20 | GND | Ground connection. |
| 21 | AN17 | 2.0 mA anode output. |
| 22 | AN18 | 2.0 mA anode output. |
| 23 | AN19 | 2.0 mA anode output. |
| 24 | AN20 | 2.0 mA anode output. |
| 25 | AN21 | 2.0 mA anode output. |
| 26 | AN22 | 2.0 mA anode output. |
| 27 | AN23 | 2.0 mA anode output. |
| 28 | AN24 | 20 mA anode output. |
| 29 | AN25 | 20 mA anode output. |
| 30 | AN26 | 20 mA anode output. |
| 31 | AN27 | 20 mA anode output. |
| 32 | AN28 | 20 mA anode output. |
| 33 | AN29 | 20 mA anode output. |
| 34 | AN30 | 2.0 mA anode output. |
| 35 | $\mathrm{DIN}_{\text {IN }}$ | Shift register data input. |
| 36 | CLK | Shift register clock input. |
| 37 | STB | Transfer contents of shift registers to output stages. |
| 38 | GREN | Grid outputs enable. |
| 39 | AN31 | 2.0 mA anode output. |
| 40 | $\mathrm{V}_{\mathrm{BB}}$ | Supply voltage input. |



Figure 2. Block Diagram

## OPERATION DESCRIPTION

Upon the initial application of power, the power on reset function will cause all of the anode and grid driver outputs to be off and all shift register outputs to be set low. Data is fed into the shift register through the $\mathrm{D}_{\mathrm{IN}}$ pin at the rising edge of the CLK input. Thirty four bits of data are capable of being stored by the shift register. Once the desired pattern is stored in the shift register, it can be transferred to the latch by setting the STB input high. The output of each latch drives its corresponding output stage. A logic high input to the shift register/latch will cause the corresponding output to turn on. A logic low input to the shift register/latch will
cause the corresponding output to turn off. Please note that if the STB is held high, the outputs of the latch reflect the outputs of the corresponding shift register bits and will change if data is shifted in.
The three GRID outputs are gated by the GREN input. When GREN is low, the GRID outputs are forced low regardless of the state of the corresponding latch output. When GREN is high, the GRID outputs correspond to the state of their respective latch outputs. The anode outputs, AN1 to AN31 are always enabled.

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## APPLICATION INFORMATION

Table 1. Bit Pattern, G = Grid, $\mathbf{A}=$ Anode.

| Bit \# | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 | 12 | 13 | 14 | 15 | 16 | 17 |
| :--- | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Pin Name | G1 | G2 | G3 | A1 | A2 | A3 | A4 | A5 | A6 | A7 | A8 | A9 | A10 | A11 | A12 | A13 | A14 |


| Bit \# | 18 | 19 | 20 | 21 | 22 | 23 | 24 | 25 | 26 | 27 | 28 | 29 | 30 | 31 | 32 | 33 | 34 |
| :--- | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Pin Name | A15 | A16 | A17 | A18 | A19 | A20 | A21 | A22 | A23 | A24 | A25 | A26 | A27 | A28 | A29 | A30 | A31 |


$\qquad$


ANODES $\qquad$


* Selected grid goes high only if input bit pattern from shift register to grid is high.

Figure 3. Typical Operation

Unused grid and anode drivers should have their respective bits set to logic low in the data stream.

Multiple grid or anode drivers may be connected together, but must be programmed to the same logic state for proper
device operation. Maximum package power must be observed and care must be taken to maintian junction temperature below $+150^{\circ} \mathrm{C}$.

MARKING DIAGRAMS

CS1088
AWLYYWW $\quad \begin{array}{ll}\text { DIP-40 } \\ \text { WIDE BODY } \\ \text { NSUFFIX } \\ \text { CASE 711 }\end{array}$

PIN CONNECTIONS


## PACKAGE DIMENSIONS

DIP-40
WIDE BODY
N SUFFIX
CASE 711-03
ISSUE C


NOTES:

1. POSITIONAL TOLERANCE OF LEADS (D), SHALL BE WITHIN 0.25 (0.010) AT MAXIMUM MATERIAL CONDITION, IN RELATION TO SEATING PLANE AND EACH OTHER.
2. DIMENSION LTO CENTER OF LEADS WHEN FORMED PARALLEL
3. DIMENSION B DOES NOT INCLUDE MOLD FLASH

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
| A | 51.69 | 52.45 | 2.035 | 2.065 |
| B | 13.72 | 14.22 | 0.540 | 0.560 |
| C | 3.94 | 5.08 | 0.155 | 0.200 |
| D | 0.36 | 0.56 | 0.014 | 0.022 |
| F | 1.02 | 1.52 | 0.040 | 0.060 |
| G | 2.54 BSC |  | 0.100 BSC |  |
| H | 1.65 | 2.16 | 0.065 | 0.085 |
| J | 0.20 | 0.38 | 0.008 | 0.015 |
| K | 2.92 | 3.43 | 0.115 | 0.135 |
| L | 15.24 BSC |  | 0.600 BSC |  |
| M | $0^{\circ}$ | $15^{\circ}$ | $0^{\circ}$ | $15^{\circ}$ |
| N | 0.51 | 1.02 | 0.020 | 0.040 |

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